

# HD74HC01

Quad. 2-input NAND Gates (with open drain outputs)

REJ03D0532-0200  
 (Previous ADE-205-404)  
 Rev.2.00  
 Oct 06, 2005

## Features

- High Speed Operation:  $t_{pd} = 9 \text{ ns typ (} C_L = 50 \text{ pF)}$
- High Output Current: Fanout of 10 LSTTL Loads
- Wide Operating Voltage:  $V_{CC} = 2 \text{ to } 6 \text{ V}$
- Low Input Current:  $1 \mu\text{A max}$
- Low Quiescent Supply Current:  $I_{CC} \text{ (static)} = 1 \mu\text{A max (} T_a = 25^\circ\text{C)}$
- Ordering Information

Part Name	Package Type	Package Code (Previous Code)	Package Abbreviation	Taping Abbreviation (Quantity)
HD74HC01P	DILP-14 pin	PRDP0014AB-B (DP-14AV)	P	—
HD74HC01FPEL	SOP-14 pin (JEITA)	PRSP0014DF-B (FP-14DAV)	FP	EL (2,000 pcs/reel)
HD74HC01RPEL	SOP-14 pin (JEDEC)	PRSP0014DE-A (FP-14DNV)	RP	EL (2,500 pcs/reel)

Note: Please consult the sales office for the above package availability.

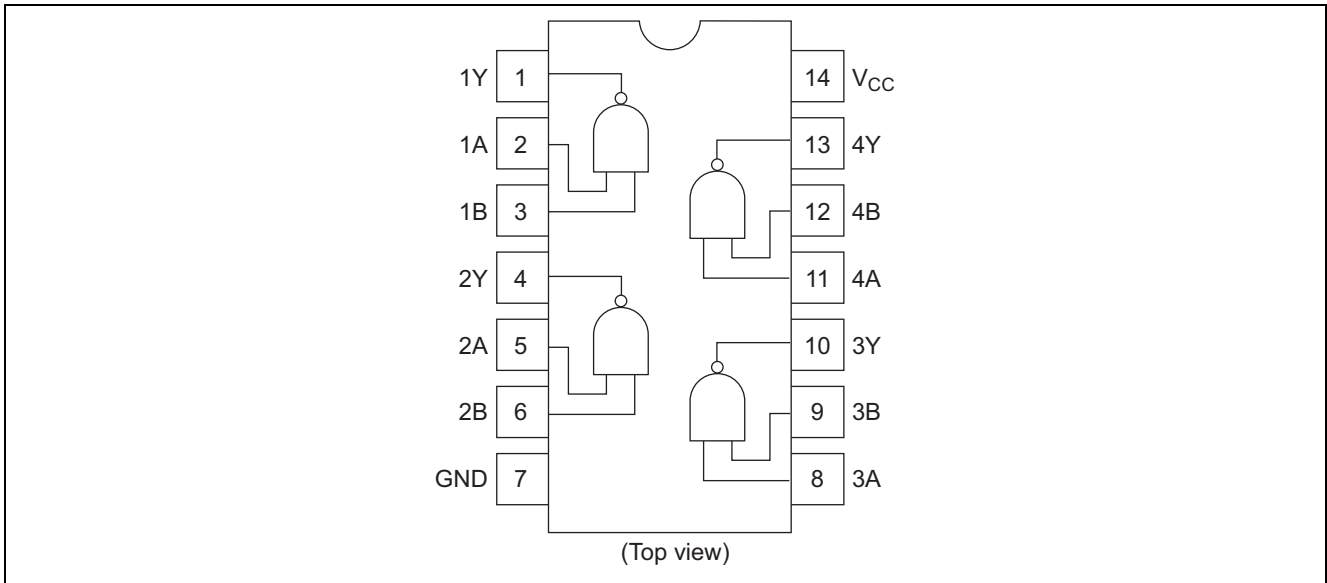
## Function Table

Inputs		Output
A	B	Y
L	L	H
L	H	H
H	L	H
H	H	L

H : High level

L : Low level

## Pin Arrangement



## Absolute Maximum Ratings

Item	Symbol	Ratings	Unit
Supply voltage range	$V_{CC}$	-0.5 to 7.0	V
Input / Output voltage	$V_{in}, V_{out}$	-0.5 to $V_{CC} + 0.5$	V
Input / Output diode current	$I_{IK}, I_{OK}$	$\pm 20$	mA
Output current	$I_o$	$\pm 25$	mA
$V_{CC}$ , GND current	$I_{CC}$ or $I_{GND}$	$\pm 50$	mA
Power dissipation	$P_T$	500	mW
Storage temperature	$T_{stg}$	-65 to +150	$^{\circ}C$

Note: The absolute maximum ratings are values, which must not individually be exceeded, and furthermore, no two of which may be realized at the same time.

## Recommended Operating Conditions

Item	Symbol	Ratings	Unit	Conditions
Supply voltage	$V_{CC}$	2 to 6	V	
Input / Output voltage	$V_{IN}, V_{OUT}$	0 to $V_{CC}$	V	
Operating temperature	$T_a$	-40 to 85	$^{\circ}C$	
Input rise / fall time <sup>*1</sup>	$t_r, t_f$	0 to 1000	ns	$V_{CC} = 2.0 V$
		0 to 500		$V_{CC} = 4.5 V$
		0 to 400		$V_{CC} = 6.0 V$

Note: 1. This item guarantees maximum limit when one input switches.  
Waveform: Refer to test circuit of switching characteristics.

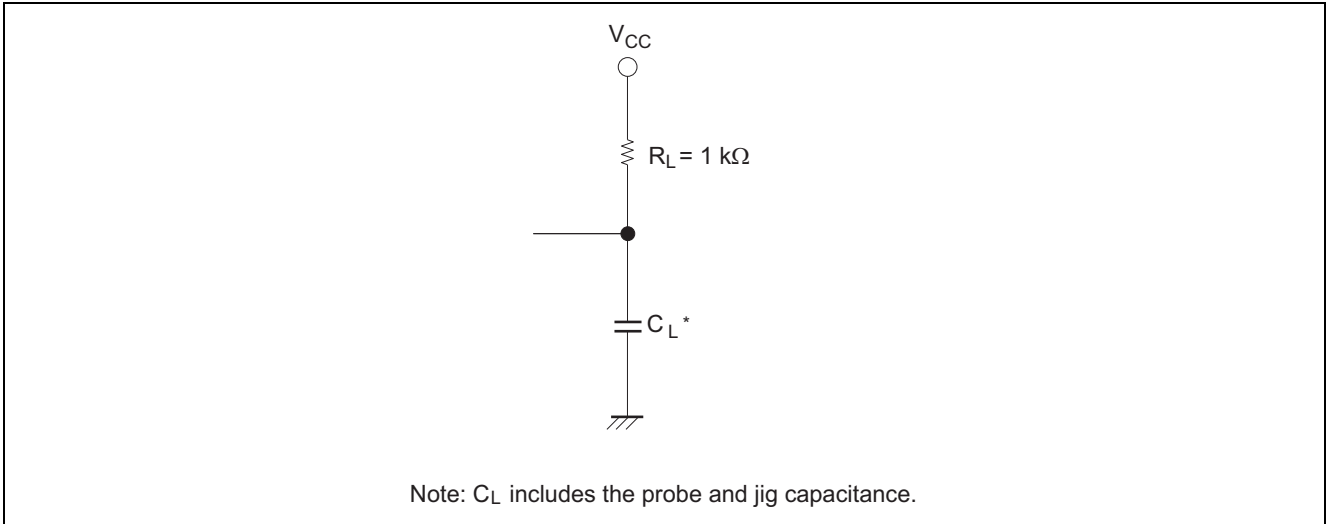
## Electrical Characteristics

Item	Symbol	V <sub>CC</sub> (V)	Ta = 25°C			Ta = -40 to +85°C		Unit	Test Conditions	
			Min	Typ	Max	Min	Max			
Input voltage	V <sub>IH</sub>	2.0	1.5	—	—	1.5	—	V		
		4.5	3.15	—	—	3.15	—			
		6.0	4.2	—	—	4.2	—			
	V <sub>IL</sub>	2.0	—	—	0.5	—	0.5	V		
		4.5	—	—	1.35	—	1.35			
		6.0	—	—	1.8	—	1.8			
Output voltage	V <sub>OL</sub>	2.0	—	0.0	0.1	—	0.1	V	V <sub>in</sub> = V <sub>IH</sub> or V <sub>IL</sub>	I <sub>OL</sub> = 20 μA
		4.5	—	0.0	0.1	—	0.1			I <sub>OL</sub> = 4 mA
		6.0	—	0.0	0.1	—	0.1			
		4.5	—	—	0.26	—	0.33			
		6.0	—	—	0.26	—	0.33			
Off-state output current	I <sub>o(off)</sub>	6.0	—	—	±0.5	—	±5.0	μA	V <sub>in</sub> = V <sub>IH</sub> or V <sub>IL</sub> , V <sub>out</sub> = V <sub>CC</sub> or GND	
Input current	I <sub>in</sub>	6.0	—	—	±0.1	—	±1.0	μA	V <sub>in</sub> = V <sub>CC</sub> or GND	
Quiescent supply current	I <sub>CC</sub>	6.0	—	—	1.0	—	10	μA	V <sub>in</sub> = V <sub>CC</sub> or GND, I <sub>out</sub> = 0 μA	

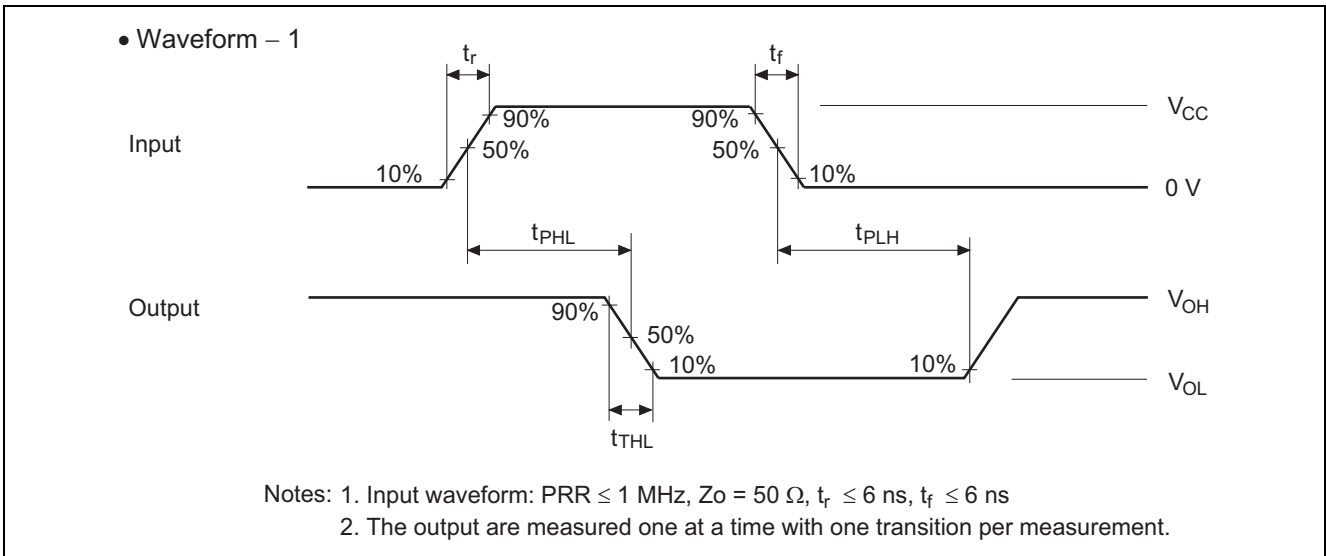
## Switching Characteristics (C<sub>L</sub> = 50 pF, Input t<sub>r</sub> = t<sub>f</sub> = 6 ns)

Item	Symbol	V <sub>CC</sub> (V)	Ta = 25°C			Ta = -40 to +85°C		Unit	Test Conditions	
			Min	Typ	Max	Min	Max			
Propagation delay time	t <sub>PLH</sub>	2.0	—	—	90	—	115	ns		
		4.5	—	11	18	—	23			
		6.0	—	—	15	—	20			
	t <sub>PHL</sub>	2.0	—	—	90	—	112	ns		
		4.5	—	7	18	—	22			
		6.0	—	—	15	—	18			
Output fall time	t <sub>THL</sub>	2.0	—	—	75	—	95	ns		
		4.5	—	5	15	—	19			
		6.0	—	—	13	—	16			
Input capacitance	C <sub>in</sub>	—	—	5	10	—	10	pF		

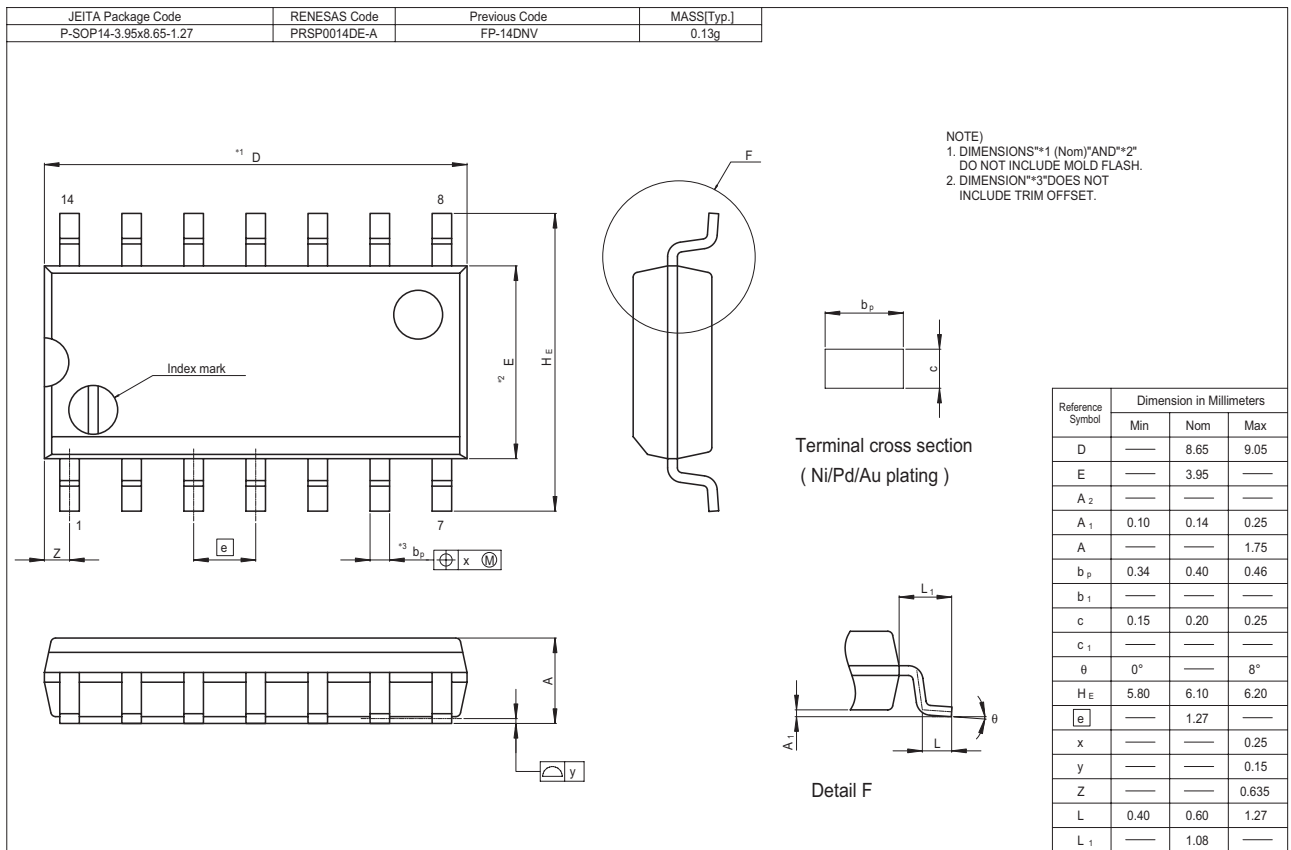
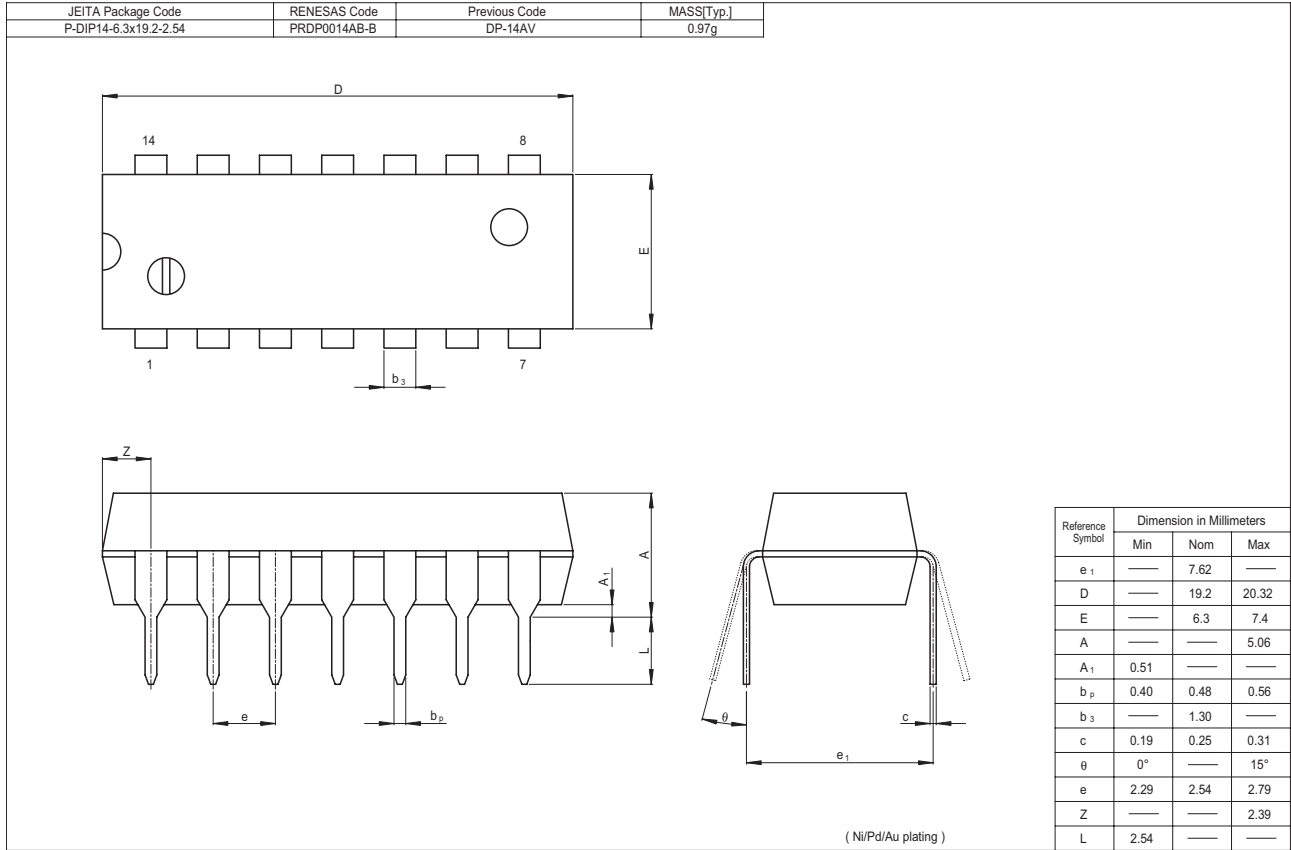
Test Circuit



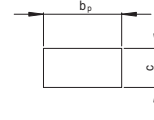
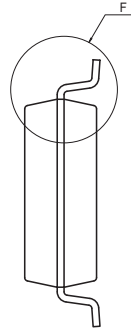
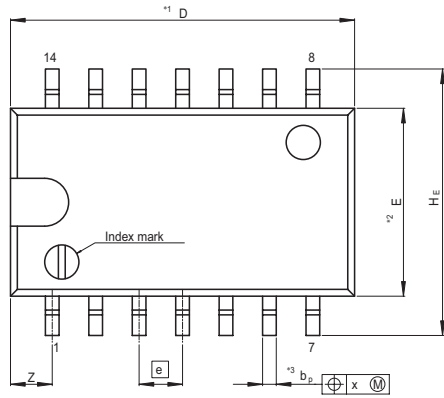
Waveforms



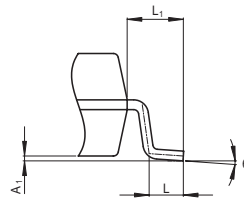
Package Dimensions



JEITA Package Code P-SOP14-5.5x10.06-1.27	RENESAS Code PRSP0014DF-B	Previous Code FP-14DAV	MASS[Typ.] 0.23g
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Terminal cross section  
( Ni/Pd/Au plating )



Detail F

NOTE)  
1. DIMENSIONS\*1 (Nom)\*AND\*2\*  
DO NOT INCLUDE MOLD FLASH.  
2. DIMENSION\*3\*DOES NOT  
INCLUDE TRIM OFFSET.

Reference Symbol	Dimension in Millimeters		
	Min	Nom	Max
D	—	10.06	10.5
E	—	5.50	—
A <sub>2</sub>	—	—	—
A <sub>1</sub>	0.00	0.10	0.20
A	—	—	2.20
b <sub>p</sub>	0.34	0.40	0.46
b <sub>1</sub>	—	—	—
c	0.15	0.20	0.25
c <sub>1</sub>	—	—	—
θ	0°	—	8°
H <sub>E</sub>	7.50	7.80	8.00
e	—	1.27	—
x	—	—	0.12
y	—	—	0.15
Z	—	—	1.42
L	0.50	0.70	0.90
L <sub>1</sub>	—	1.15	—

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